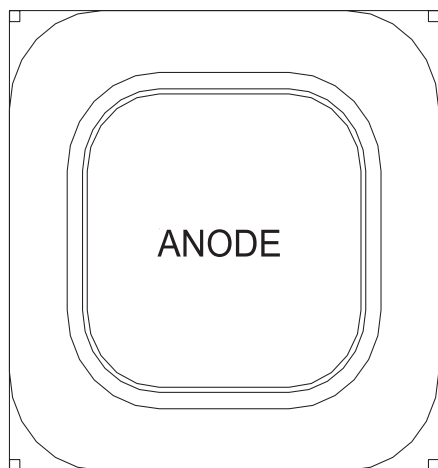


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14 x 14 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	9.0 x 9.0 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER

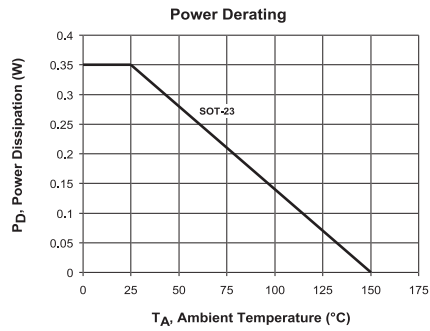
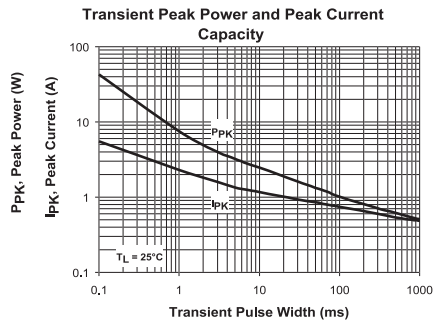
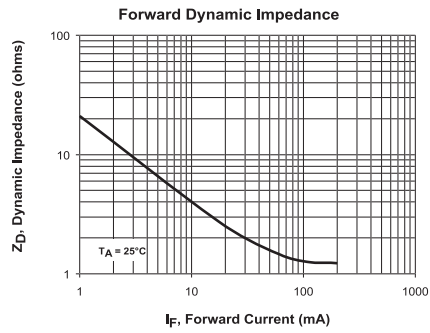
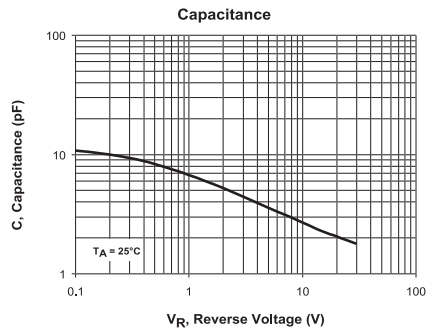
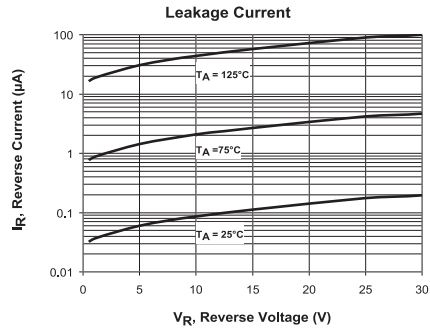
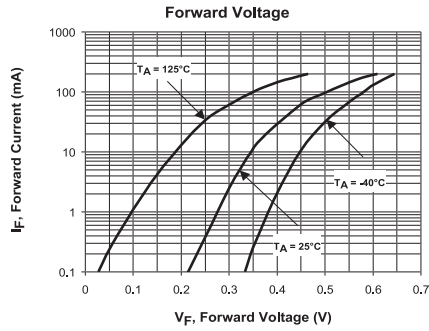
62,250

PRINCIPAL DEVICE TYPES

CMP SH-3 Series
CMSSH-3 Series
CMXSH-3
CMKSH-3T

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R0 (13- February 2006)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R0 (13- February 2006)